## Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary) U.S. PATENTER EXAMINER DOCUMENT DATE

Docket Number (Optional) 3259.1US (91-473.02 RE)

Application Number
Not Yet Assigned

Applicant Dennison et al.

Filing Date December 12, 2001

Group Art Unit **Unknown** 

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATI
N	4,432,799	02/1984	Salazar			TO TO
TN,	4,671,851	06/1987	Beyer et al.			
TN	4,785,337	11/1988	Kenney		<del></del>	=
Tar	4,877,750	10/1989	Okumura			
TN	4,944,836	07/1990	Beyer et al.			α (
TN	5,045,899	09/1991	Arimoto et al.	_		
TN	5,150,276	09/1992	Gonzalez et al.		<del></del>	
77/	_5,1 <del>62,248</del>	11/1992	Dennison et al-			
TN	5,162,248	11/1992	Dennison et al.			
TN	5,185,282	02/1993	Lee et al.		->	
m,	5,313,089	05/1994	Jones, Jr.			
'W	5 364 809	11/1994	Kwon et al.		_	

	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
	NUMBER	DATE	COOMIN			YES	NO
TN	0286270	12/1987	JP			,	
TA	0074752	03/1989	JP				
TO	0094554	04/1990	JP		<b>_</b>		

	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
TN	"Stacked Capacitor DRAM Cell with Vertical Fins," IBM TDB, Jul. 1990, pp. 245-247.
7~	Kaga, T., et al., "Crown-Shaped Stacked-Capacitor Cell for 1.5-V Operation 64 Mb Dram's", <u>IEEE Transactions on Electron Devices</u> , vol. 38, No. 2, Feb. 1991, pp. 255-261.
TN	Shinmura, N., et al., "A Stacked Capacitor Cell with Ring Structure", Extended abstracts of the 22 <sup>nd</sup> International Conference on Solid State Devices, pp.833-836, 1990.

EXAMINER T. NGUYEN

DATE CONSIDERED 4/17/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.